Listing of Claims:

1. (Currently Amended) ~~Method~~ A method for depositing a material (3) on a substrate wafer (1) having the following method steps:

(a) providing ~~provision of~~ the substrate wafer (1), which has a growth area (4) intended for a later material deposition[[,]];

(b) applying ~~application of~~ a thermal radiation absorption layer (2), which exhibits a good absorption of thermal radiation, on ~~the~~ a rear side (5) of the substrate wafer (1) [[,]] which faces away from the growth area (4)[[,]];

(c) heating ~~of~~ the substrate wafer (1) to ~~the~~ a deposition temperature[[,]];

(d) depositing ~~deposition of~~ a material (3) onto the growth area (4) of the substrate wafer (1) by an MOVPE method;

wherein the thermal radiation absorption layer is applied before deposition of the material onto the growth area of the substrate wafer.

2. (Currently Amended) ~~Method~~ The method according to Claim 1, in which the deposited material (3) ~~to be deposited~~ is a semiconductor material.

3. (Currently Amended) ~~Method~~ The method according to Claim 1, in which the deposited material (3) ~~to be deposited~~ comprises at least one layer made of $Al_xGa_yIn_{1-x-y}N$, where $0 \leq x+y \leq 1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$ apply.

4. (Currently Amended) ~~Method~~ The method according to claim 1, in which a substrate wafer is used which essentially comprises SiC or an SiC-based material.

5. (Currently Amended) ~~Method~~ The method according to claim 1,

in which a material or a material mixture which exhibits inert behaviour during the deposition method in accordance with method step (d) is applied as the thermal radiation absorption layer (2).

6. (Currently Amended) ~~Method~~ The method according to claim 1,

in which a material or a material mixture which is compatible with a ~~the~~ material and/or a ~~the~~ contact-connecting process of an electrical contact that is to be applied later, is applied as the thermal radiation absorption layer (2).

7. (Currently Amended) ~~Method~~ The method according to claim 1,

in which the thermal radiation absorption layer (2) is applied by means of sputtering in accordance with method step (b).

8. (Currently Amended) ~~Method~~ The method according to claim 1,

in which a doped Si layer, in particular a highly doped Si layer, is used as the thermal radiation absorption layer (2).

9. (Currently Amended) ~~Method~~ The method according to Claim 8,

in which the Si layer is applied with a thickness which lies between 10 nm and 20 μm inclusive.

10. (Currently Amended) ~~Method~~ The method according to Claim 8,

in which the Si layer has a doping of at least $1 \times 10^{19}/cm^3$.

11. (Currently Amended) ~~Method~~ The method according to claim 1,

in which the heating in accordance with method step (c) is essentially effected by means of thermal radiation.

12. (Currently Amended) ~~Method~~ The method according to claim 1,

in which, in method step (c), a heating source is used which generates thermal radiation of a spectral range for which the thermal radiation absorption layer (2) exhibits good radiation absorption.